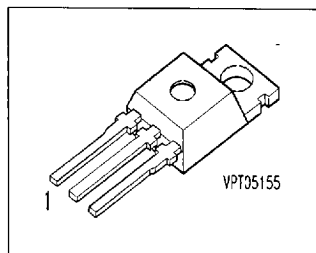


SIPMOS® Power Transistor

- N channel
- Enhancement mode



Pin 1	Pin 2	Pin 3
G	D	S

Type	V_{DS}	I_D	$R_{DS(on)}$	Package	Ordering Code
BUZ 50 B	1000 V	2 A	8 Ω	TO-220 AB	C67078-A1307-A4

Maximum Ratings

Parameter	Symbol	Values	Unit
Drain source voltage	V_{DS}	1000	V
Drain-gate voltage $R_{GS} = 20 \text{ k}\Omega$	V_{DGR}	1000	
Continuous drain current $T_C = 25^\circ\text{C}$	I_D	2	A
Pulsed drain current $T_C = 25^\circ\text{C}$	I_{Dpuls}	8	
Gate source voltage	V_{GS}	± 20	V
Power dissipation $T_C = 25^\circ\text{C}$	P_{tot}	78	W
Operating temperature	T_j	-55+ 150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55+ 150	
Thermal resistance, chip case	R_{thJC}	≤ 1.6	K/W
Thermal resistance, chip to ambient	R_{thJA}	75	
DIN humidity category, DIN 40 040		C	
IEC climatic category, DIN IEC 68-1		55 / 150 / 56	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Static Characteristics

Drain- source breakdown voltage $V_{GS} = 0\text{ V}$, $I_D = 0.25\text{ mA}$, $T_j = 25^\circ\text{C}$	$V_{(BR)DSS}$	1000	-	-	V
Gate threshold voltage $V_{GS} = V_{DS}$, $I_D = 1\text{ mA}$	$V_{GS(th)}$	2.1	3	4	
Zero gate voltage drain current $V_{DS} = 1000\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 25^\circ\text{C}$ $V_{DS} = 1000\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 125^\circ\text{C}$	I_{DSS}	- -	20 100	250 1000	μA
Gate-source leakage current $V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	-	10	100	
Drain-Source on-resistance $V_{GS} = 10\text{ V}$, $I_D = 1.5\text{ A}$	$R_{DS(on)}$	-	6.5	8	Ω

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Dynamic Characteristics

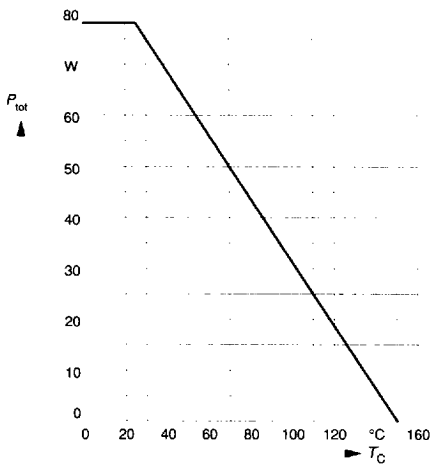
Transconductance $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 1.5 \text{ A}$	g_{fs}	0.7	1.5	-	S
Input capacitance $V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$	C_{iss}	-	1600	2100	pF
Output capacitance $V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$	C_{oss}	-	70	120	
Reverse transfer capacitance $V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$	C_{rss}	-	30	55	
Turn-on delay time $V_{DD} = 30 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 2 \text{ A}$ $R_{GS} = 50 \Omega$	$t_{d(on)}$	-	30	45	ns
Rise time $V_{DD} = 30 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 2 \text{ A}$ $R_{GS} = 50 \Omega$	t_r	-	40	60	
Turn-off delay time $V_{DD} = 30 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 2 \text{ A}$ $R_{GS} = 50 \Omega$	$t_{d(off)}$	-	110	140	
Fall time $V_{DD} = 30 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 2 \text{ A}$ $R_{GS} = 50 \Omega$	t_f	-	60	80	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Reverse Diode					
Inverse diode continuous forward current $T_C = 25\text{ }^{\circ}\text{C}$	I_S	-	-	2	A
Inverse diode direct current,pulsed $T_C = 25\text{ }^{\circ}\text{C}$	I_{SM}	-	-	8	
Inverse diode forward voltage $V_{GS} = 0\text{ V}$, $I_F = 6\text{ A}$	V_{SD}	-	1.05	1.3	V
Reverse recovery time $V_R = 100\text{ V}$, $I_F = I_S$, $di_F/dt = 100\text{ A}/\mu\text{s}$	t_{rr}	-	2	-	μs
Reverse recovery charge $V_R = 100\text{ V}$, $I_F = I_S$, $di_F/dt = 100\text{ A}/\mu\text{s}$	Q_{rr}	-	15	-	μC

Power dissipation

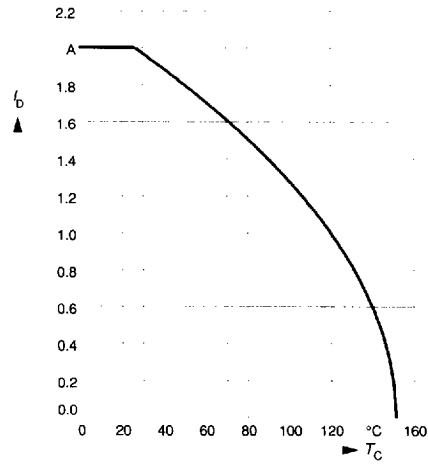
$P_{tot} = f(T_C)$



Drain current

$I_D = f(T_C)$

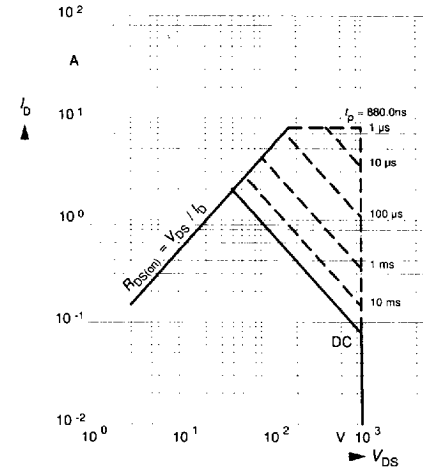
parameter: $V_{GS} \geq 10\text{ V}$



Safe operating area

$I_D = f(V_{DS})$

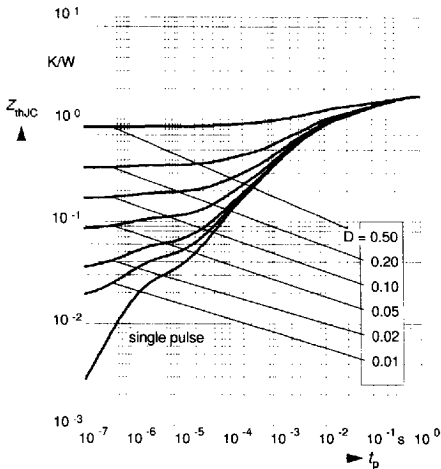
parameter: $D = 0.01$, $T_C = 25^\circ\text{C}$



Transient thermal impedance

$Z_{thJC} = f(t_p)$

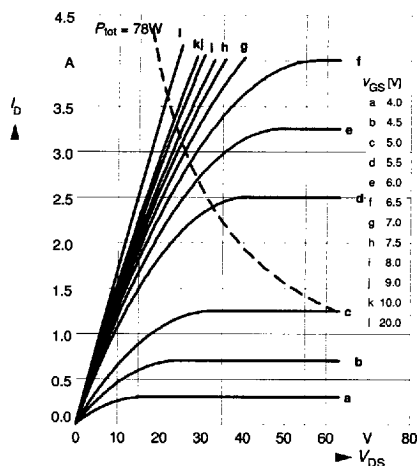
parameter: $D = t_p / T$



Typ. output characteristics

$$I_D = f(V_{DS})$$

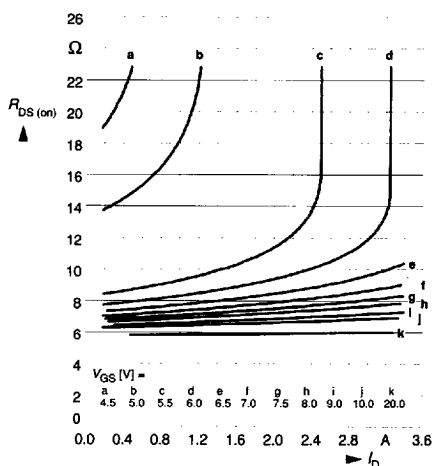
parameter: $t_p = 80 \mu s$



Typ. drain-source on-resistance

$$R_{DS(on)} = f(I_D)$$

parameter: V_{GS}

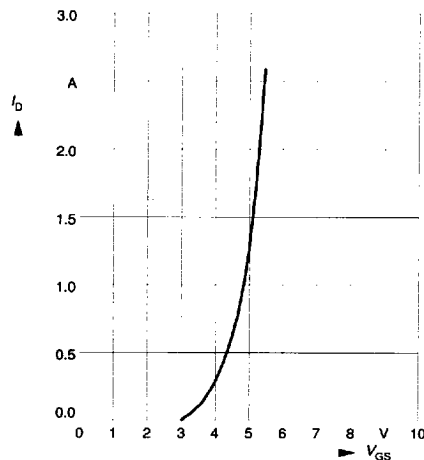


Typ. transfer characteristics

$$I_D = f(V_{GS})$$

parameter: $t_p = 80 \mu s$

$$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

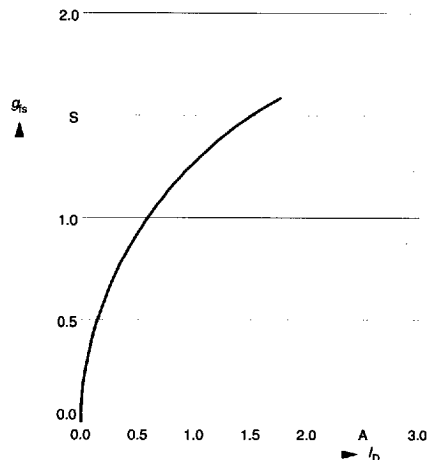


Typ. forward transconductance

$$g_{fs} = f(I_D)$$

parameter: $t_p = 80 \mu s$,

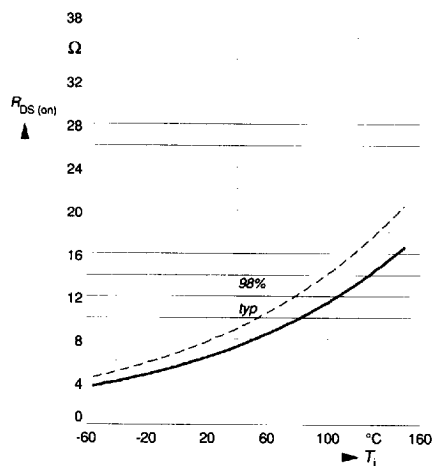
$$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$



Drain-source on-resistance

$$R_{DS(on)} = f(T_j)$$

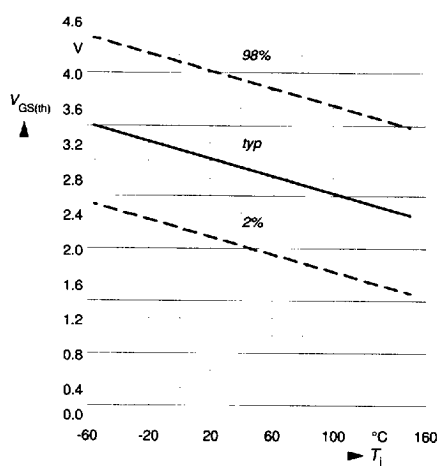
parameter: $I_D = 1.5 \text{ A}$, $V_{GS} = 10 \text{ V}$



Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

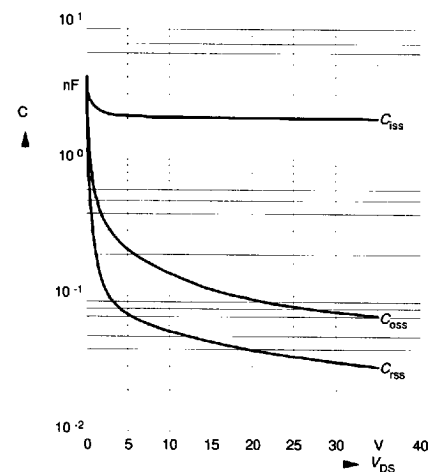
parameter: $V_{GS} = V_{DS}$, $I_D = 1 \text{ mA}$



Typ. capacitances

$$C = f(V_{DS})$$

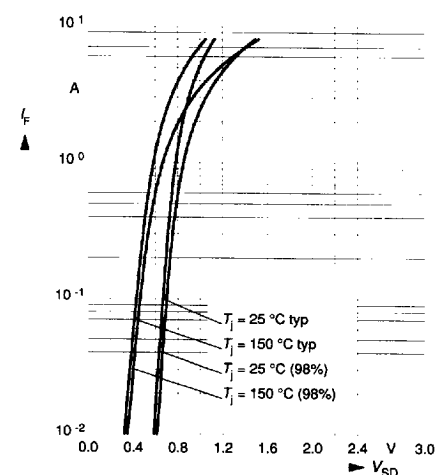
parameter: $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$



Forward characteristics of reverse diode

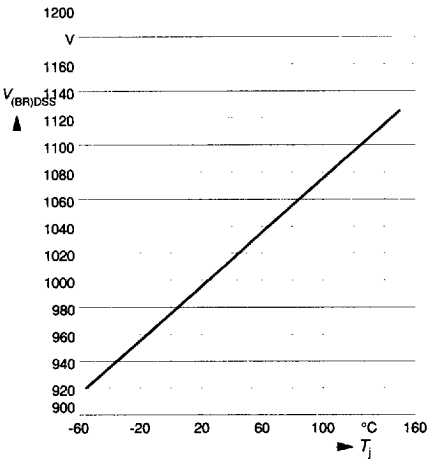
$$I_F = f(V_{SD})$$

parameter: $T_j, t_p = 80 \mu\text{s}$



Drain-source breakdown voltage

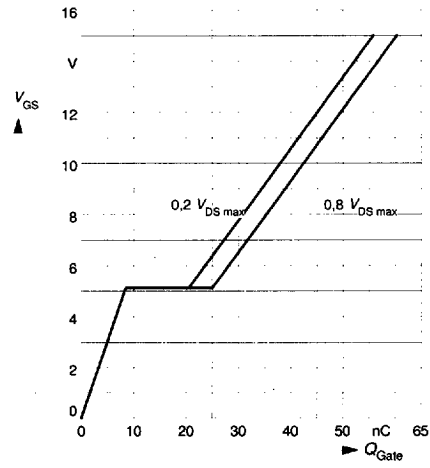
$V_{(BR)DSS} = f(T_j)$

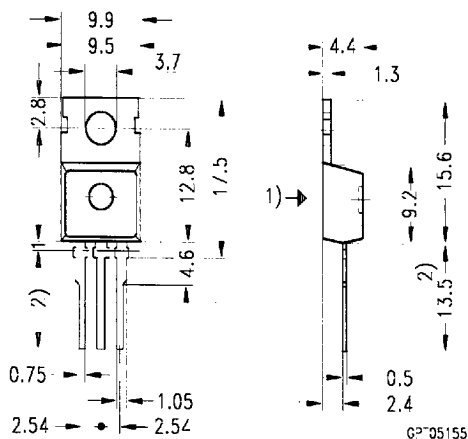


Typ. gate charge

$V_{GS} = f(Q_{Gate})$

parameter: $I_D \text{ puls} = 4 \text{ A}$



Package Outlines
TO-220 AB
Dimension in mm


1) punch direction, burr max. 0.04

2) dip tinning

3) max. 4.5 by dip tinning press burr max. 0.05